

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Cancelled)
2. (Cancelled)
3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (Cancelled)
7. (Cancelled)
8. (Cancelled)
9. (Cancelled)
10. (Cancelled)
11. (Cancelled)
12. (Cancelled)
13. (Cancelled)
14. (Cancelled)
15. (Previously Presented) A method of testing the effect of lights having different wavelengths on a layer of photoresist, comprising:

providing a phase-shifting mask having a transparent material having first and second trenches, the first trench having a first depth and the second trench having a second depth deeper than the first depth;

transmitting light having a first wavelength through the first trench to the photoresist layer such that the light having a first wavelength is phase-shifted;

transmitting light having a second wavelength longer than the first wavelength through the second trench to the photoresist layer such that the light having a second wavelength is phase-shifted; and

comparing an effect on the photoresist layer of the light having the first wavelength to an effect on the photoresist layer of the light having the second wavelength.

16. (Previously Presented) The method of claim 15, wherein the first depth is suitable for phase-shifting light having the wavelength of 248 nm by 180 degrees.

17. (Previously Presented) The method of claim 15, wherein the first depth is suitable for phase-shifting the first light by 180 degrees and the second depth is suitable for phase-shifting the second light by 180 degrees.

18. (Previously Presented) The method of claim 15, wherein the first depth is suitable for phase-shifting light having a wavelength of 193 nm.

19. (Original) The method of claim 15, wherein the transparent material includes a first region of trenches including the first trench, the first region of trenches including a plurality of trenches having the first depth, wherein the transparent material includes a second region of trenches including the second trench, the second region of trenches including a plurality of trenches having the second depth.

20. (Original) The method of claim 19, wherein the first region comprises at least one-fourth of the transparent material and the second region comprises at least one-fourth of the transparent material.

21. (Original) The method of claim 19, wherein the first region comprises approximately one-half of the transparent material and the second region comprises approximately one-half of the transparent material.

22. (Original) The method of claim 15, wherein the phase-shifting mask includes an opaque layer coupled to the transparent material, the opaque layer representing a printed circuit pattern.

23. (New) A method of using a phase-shifting mask comprising:
transmitting light having a first wavelength through a first set of trenches provided in a phase-shifting mask to a layer of material such that the light having a first wavelength is phase-shifted, the first set of trenches having a first depth;
transmitting light having a second wavelength longer than the first wavelength through a second set of trenches provided in the phase-shifting mask to the layer of material such that the light having a second wavelength is phase-shifted, the second set of trenches have a second depth greater than the first depth; and
comparing patterns provided in the layer of material by the light having the first wavelength and by the light having the second wavelength.

24. (New) The method of claim 23, wherein the step of comparing patterns provided in the layer of material comprises utilizing a scanning electron microscope.

25. (New) The method of claim 23, wherein the layer of material comprises a photoresist material.

26. (New) The method of claim 23, wherein the first depth is suitable for phase-shifting light having a wavelength of 248 nm by 180 degrees.

27. (New) The method of claim 23, wherein the first depth is suitable for phase-shifting the first light by 180 degrees and the second depth is suitable for phase-shifting the second light by 180 degrees.

28. (New) The method of claim 23, wherein the first depth is suitable for phase-shifting light having a wavelength of 193 nm by 180 degrees.

29. (New) The method of claim 23, wherein the phase-shifting mask comprises a transparent material and includes a first region including the first set of trenches and a second region including the second set of trenches.

30. (New) The method of claim 29, wherein the first region comprises at least one-fourth of the phase-shifting mask and the second region comprises at least one-fourth of the phase-shifting mask.

31. (New) The method of claim 29, wherein the first region comprises approximately one-half of the phase-shifting mask and the second region comprises approximately one-half of the phase-shifting mask.

32. (New) The method of claim 29, wherein the phase-shifting mask includes an opaque layer coupled to the transparent material, the opaque layer representing a printed circuit pattern.

33. (New) A method for using a phase-shifting mask to test the effects of light having different wavelengths comprising:

providing a phase-shifting mask comprising a transparent material, the phase shifting mask comprising a plurality of first trenches having a first depth and a plurality of second trenches have a second depth deeper than the first depth;

passing light having a first wavelength through the plurality of first trenches to a layer comprising photoresist material such that the light having a first wavelength is phase-shifted;

passing light having a second wavelength longer than the first wavelength through the plurality of second trenches to the layer comprising photoresist material such that the light having a second wavelength is phase-shifted;

analyzing the layer of photoresist material to determine the effects of the light having the first wavelength and of the light having the second wavelength.

34. (New) The method of claim 33, wherein the phase-shifting mask includes a first area comprising the plurality of first trenches, the first area comprising at least one-fourth of the phase-shifting mask.

35. (New) The method of claim 34, wherein the first area comprises at least one-half of the phase-shifting mask.

36. (New) The method of claim 33, wherein the phase-shifting mask comprises an opaque layer provided over the transparent material.

37. (New) The method of claim 33, wherein the first depth is suitable to phase-shift the light having a first wavelength by 180 degrees and the second depth is suitable to phase-shift the light having a second wavelength by 180 degrees.